









B2D06065E

650V ▲ 6A ▲ SIC SCHOTTKY DIODE

SILICON CARBIDE SIC SCHOTTKY DIODE ▲ SMD type

Excellent surge capability

Easy paralleling due to positive V_F temperature coefficient

TO-252-2L (DPAK) package ▲ Epoxy meets UL94-V0 ▲ MSL3

Temperature independent switching

Ultra-low forward voltage and high surge current

SPECIFICATION

Item (T _c = 25°C, unless otherwise noted)	Characteristics	
Operating Temperature Range	T _J	-55°C to +175°C
Storage Temperature Range	Ts	-55°C to +175°C
Repetitive Peak Reverse Voltage		650V
Continuous Forward Current at T _c = 160°C	I _F	6A
Total Capacitive Charge (T _J = 25°C)	\mathbf{Q}_{c}	17nC
Capacitance Stored Energy (V _R = 400V)	Ec	4.5μJ
Diode Forward Voltage (T _J = 175°C, I _F = 6A)		1.63V
Power Dissipation	P _{TOT}	107W

APPLICATIONS

EV Charging	Industrial Inverters	Motors & Drives	Power Factor Correction	Renewable Energy	SMPS	UPS
₹ /•			PFC	*		

PIN DESCRIPTION

Circuit Diagram	Outline • Top View	Pin No.	Description
Case	Case 1 2	1 2	Cathode (Case Backside) Anode

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ABSOLUT MAXIMUM RATINGS ▲ T_C = 25°C, unless otherwise noted

Item	Condition	Symbol		Unit
Repetitive Peak Reverse Voltage		V_{RRM}	650	V
Non-Repetitive Peak Reverse Voltage		V_{RSM}	650	V
Continuous Forward Current	T _C = 25°C	I _F	24	Α
Continuous Forward Current	$T_C = 160^{\circ}C$	I _F	6	Α
Non-Repetitive Forward Surge Current	T_C = 25°C, t_p = 10ms, Half Sine Wave	I _{FSM}	48	Α
I ² t Value	$T_C = 25^{\circ}C$, $t_p = 10$ ms	∫i²dt	11.52	A^2s
Power Dissipation	T _C = 25°C	P _{TOT}	107	W
Power Dissipation	$T_C = 110^{\circ}C$	P_{TOT}	46	W
Operating Junction Temperature		T _J	-55 to +175	°C
Storage Temperature Range		T_{STG}	-55 to +175	°C

ELECTRICAL CHARACTERISTICS

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Static Characteristics						
DC Blocking Voltage	T _J = 25°C	V_{DC}	650			V
Diode Forward Voltage	$I_F = 6A, T_J = 25^{\circ}C$	V_{F}		1.33	1.50	V
Diode Forward Voltage	$I_F = 6A, T_J = 175^{\circ}C$	V_{F}		1.63	2.10	V
Reverse Current	$V_R = 650V, T_J = 25^{\circ}C$	I_R		1	70	μΑ
Reverse Current	$V_R = 650V$, $T_J = 175$ °C	I_R		15	150	μΑ
Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Dynamic Characteristics						
	$V_R = 400V, T_J = 25^{\circ}C$					
Total Capacitive Charge	$T_{J} = 25^{\circ}C \qquad V_{DC} \qquad 650$ $I_{F} = 6A, T_{J} = 25^{\circ}C \qquad V_{F}$ $I_{F} = 6A, T_{J} = 175^{\circ}C \qquad V_{F}$ $V_{R} = 650V, T_{J} = 25^{\circ}C \qquad I_{R}$ $V_{R} = 650V, T_{J} = 175^{\circ}C \qquad I_{R}$ $V_{R} = 650V, T_{J} = 175^{\circ}C \qquad I_{R}$ $V_{R} = 400V, T_{J} = 25^{\circ}C \qquad Q_{C}$ $Q_{C} = \int_{0}^{V_{R}} C(V) dV \qquad Q_{C}$ $V_{R} = 1V, f = 1MHz, T_{J} = 25^{\circ}C \qquad C$ $V_{R} = 300V, f = 1MHz, T_{J} = 25^{\circ}C \qquad C$ $V_{R} = 600V, f = 1MHz, T_{J} = 25^{\circ}C \qquad C$	17		nC		
Total Capacitance	$V_R = 1V$, $f = 1MHz$, $T_J = 25$ °C	С		271		pF
Total Capacitance	$V_R = 300V$, $f = 1MHz$, $T_J = 25$ °C	С		30.1		pF
Total Capacitance	V_R = 600V, f = 1MHz, T_J = 25°C	С		29.8		pF
Capacitance Stored Energy	$V_R = 400V, T_J = 25^{\circ}C$	E _C		4.5		μͿ

THERMAL RESISTANCE PERFORMANCE

Item	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance, Junction to Case	$R_{\theta,JC}$		1.401		K/W



REFERENCE DATA A TYPICAL PERFORMANCE

Fig. 1 • Typical Forward Characteristics IF vs. VF

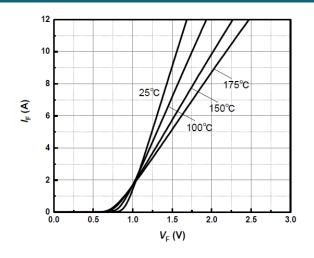


Fig. 2 • Typical Reverse Current I_R as function of Reverse Voltage V_R

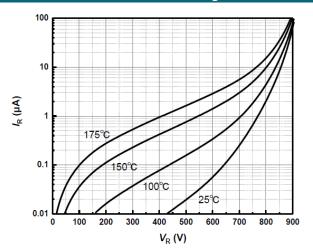


Fig. 3 • Diode Forward Current I_F as function of Case Temperature T_C (D = Duty Cycle)

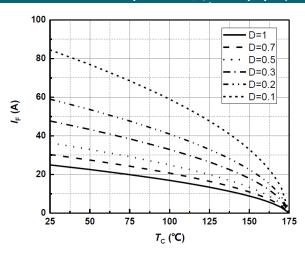


Fig. 4 • Typical Capacitance C as function of Reverse Voltage V_R , $C = f(V_R)$, $T_J = 25^{\circ}C$, f = 1MHz

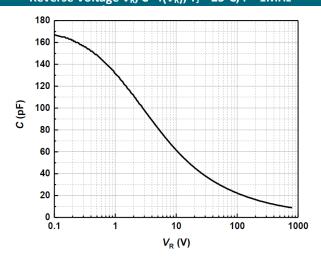


Fig. 5 • Typical Reverse Charge Q_C as function of Reverse Voltage V_R

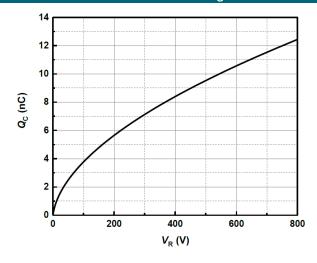
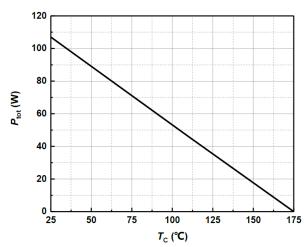


Fig. 6 • Power Dissipation P_{TOT} as function of Case Temperature T_C



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REFERENCE DATA A TYPICAL PERFORMANCE

Fig. 7 • Capacitance Stored Energy

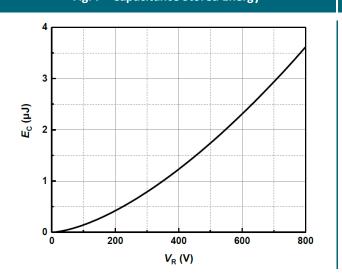
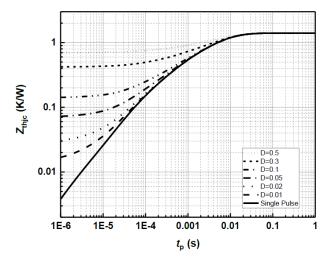
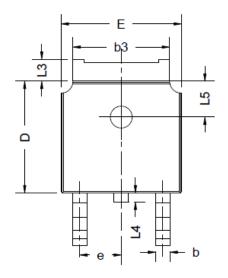


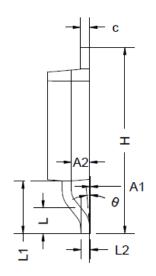
Fig. 8 • Maximum Transient Thermal Impedance, Z_{thjc} = f(t), Parameter: D = t/T

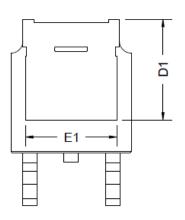


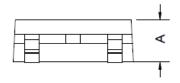


PACKAGE OUTLINE









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)		
Α	2.20	2.30	2.38		
A1	0.00	-	0.20		
A2	0.90	1.07	1.17		
b	0.68	0.78	0.90		
b3	5.23	5.33	5.46		
С	0.43	0.53	0.61		
D	5.98	6.10	6.22		
D1		5.30 REF			
E	6.40	6.60	6.73		
E1	4.63	-	-		

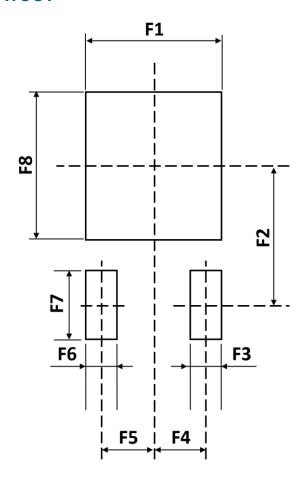
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
e		2.286 BSC	
Н	9.40	10.10	10.50
L	1.38	1.50	1.75
L1		2.90 REF	
L2		0.51 BSC	
L3	0.88	-	1.28
L4	0.50		1.00
L5	1.65	1.80	1.95
θ	0°	-	8°

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
B2D06065E	TO-252-2L (DPAK)	Reel	2,500pcs	5,000pcs	25,000pcs



RECOMMENDED PAD LAYOUT



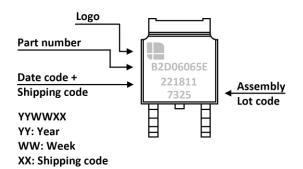
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	6.00	-
F2	-	6.25	-
F3	-	1.40	-
F4	-	2.29	-

Sym	Millimeters (Min.)	illimeters Millimeters (Min.) (Typ.)					
F5	-	2.29	-				
F6	-	1.40	-				
F7	-	3.00	-				
F8	-	6.50	-				

Notes:

- 1. The suggested land pattern dimensions have been provided for reference only.
- 2. For further information, please reference document IPC-7351A.

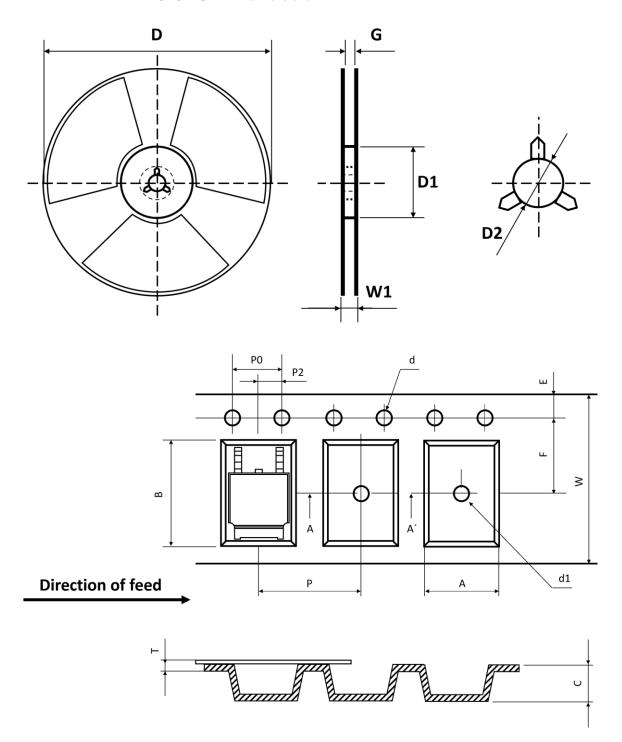
PART MARKING



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REEL AND TAPE DIMENSIONS A All dimensions in mm

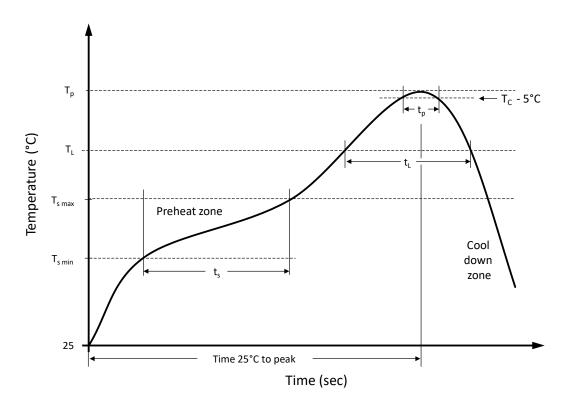


	Package	W	Α	В	С	d1	D	Е	F	Р	P0	T	D	D1	D2	G	W1
TO252-2L	16.00	6.90	10.50	2.70	1.50	1.50	1.75	7.50	8.00	4.00	0.30	330	50	13.00	16.40	22.00	
	10252-2L	±0.30	±0.10	±0.10	±0.10	Max.	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.30	Min.	±0.50	Min.	Min.

Note: All dimensions meet EIA-481-D requirements.



RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T _{s max}	150 °C	200 °C
Preheat time t _s from T _{s min} to T _{s max}	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t _L maintained above T _L	t _L	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T _L to T _p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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